

# 40 V, 1.5 A low VF MEGA Schottky barrier rectifier Rev. 2 — 6 March 2012 Prod

Product data sheet

#### 1. **Product profile**

### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a leadless ultra small SOD1608 (DFN1608D-2) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

### 1.2 Features and benefits

- Average forward current: I<sub>F(AV)</sub> ≤ 1.5 A
- Reverse voltage: V<sub>R</sub> ≤ 40 V
- Low forward voltage  $V_F \le 610 \text{ mV}$
- Low reverse current

### 1.3 Applications

Quick reference data

Table 1

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply

1.4 Quick reference data

LED backlight for mobile application

- AEC-Q101 qualified
- Solderable side pads
- Package height typ. 0.37 mm
- Ultra small and leadless SMD plastic package
- Low power consumption applications
- Ultra high-speed switching
- Reverse polarity protection

Table 1.	QUICK reference uala						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$I_{F(AV)}$	average forward current	$\delta$ = 0.5; f = 20 kHz; T <sub>amb</sub> ≤ 65 °C; square wave	<u>[1]</u>	-	-	1.5	A
		$\delta$ = 0.5; f = 20 kHz; T <sub>sp</sub> ≤ 135 °C; square wave		-	-	1.5	А
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	-	40	V
V <sub>F</sub>	forward voltage	$I_F$ = 1.5 A; pulsed; $t_p \le 300 \ \mu s$ ; δ $\le 0.02$ ; $T_j$ = 25 °C		-	540	610	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C		-	1	5	μA
t <sub>rr</sub>	reverse recovery time	$\begin{array}{l} I_{R}=0.5 \text{ A}; \ I_{F}=0.5 \text{ A}; \ I_{R(meas)}=0.1 \text{ A}; \\ T_{j}=25 \ ^{\circ}\text{C} \end{array}$		-	4	-	ns

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.



### 40 V, 1.5 A low VF MEGA Schottky barrier rectifier

### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode <sup>[1]</sup>		. 64 -
2	A	anode		1 <u>-</u> 2 sym001
			Transparent top view	
			SOD1608 (DFN1608D-2)	

[1] The marking bar indicates the cathode.

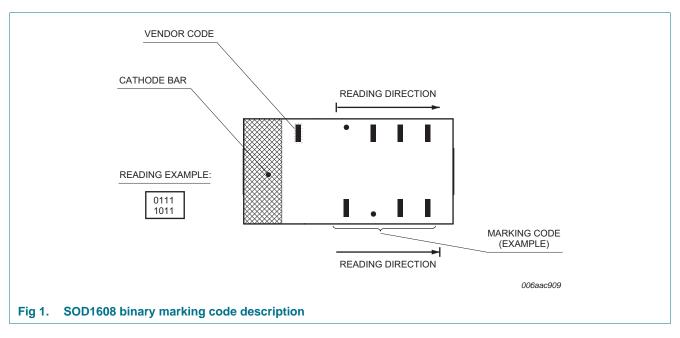
### 3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PMEG4015EPK	DFN1608D-2	Leadless ultra small plastic package; 2 terminals	SOD1608			

### 4. Marking

#### Table 4.Marking codes

Type number	Marking code
PMEG4015EPK	0110 0000



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### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
reverse voltage	,		-	40	V
forward current	T <sub>sp</sub> ≤ 130 °C		-	2.1	А
average forward current	$\delta$ = 0.5; f = 20 kHz; square wave; T <sub>amb</sub> ≤ 65 °C	<u>[1]</u>	-	1.5	A
	δ = 0.5; f = 20 kHz; square wave; T <sub>sp</sub> ≤ 135 °C		-	1.5	A
repetitive peak forward current	t <sub>p</sub> ≤ 1 ms; δ ≤ 0.25		-	4	А
non-repetitive peak forward current	$t_p$ = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	5	А
total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2][3]	-	415	mW
		[4][3]	-	895	mW
		[1][3]	-	1565	mW
junction temperature			-	150	°C
ambient temperature			-55	150	°C
storage temperature			-65	150	°C
	average forward current repetitive peak forward current non-repetitive peak forward current total power dissipation junction temperature ambient temperature	$\label{eq:product} \begin{array}{ll} \mbox{T}_{j} = 25 \ ^{\circ}\mbox{C} \\ \mbox{forward current} & $T_{sp} \leq 130 \ ^{\circ}\mbox{C} \\ \mbox{average forward current} & $\delta = 0.5; \ f = 20 \ \mbox{kHz}; \ \mbox{square wave}; \\ $T_{amb} \leq 65 \ ^{\circ}\mbox{C} \\ \hline \mbox{\delta} = 0.5; \ f = 20 \ \mbox{kHz}; \ \mbox{square wave}; \\ $T_{sp} \leq 135 \ ^{\circ}\mbox{C} \\ \hline \mbox{repetitive peak forward current} & $t_{p} \leq 1 \ \mbox{ms}; \ \mbox{\delta} \leq 0.25 \\ \mbox{non-repetitive peak forward} & $t_{p} = 8 \ \mbox{ms}; \ \mbox{T}_{j(init)} = 25 \ ^{\circ}\mbox{C}; \ \mbox{square wave} \\ \mbox{total power dissipation} & $T_{amb} \leq 25 \ ^{\circ}\mbox{C} \\ \hline \mbox{junction temperature} \\ \mbox{ambient temperature} \end{array}$	$\begin{tabular}{ c c } reverse voltage & T_j = 25 \ ^{\circ}\ C & & & & & & & & & & & & & & & & & & $	$\begin{tabular}{ c c } reverse voltage & T_{j} = 25 \ ^{\circ}\ C & -1 \\ forward current & T_{sp} \leq 130 \ ^{\circ}\ C & -1 \\ average forward current & $\delta = 0.5; \ f = 20 \ kHz; \ square wave; \\ T_{amb} \leq 65 \ ^{\circ}\ C & -1 \\ \hline $\delta = 0.5; \ f = 20 \ kHz; \ square wave; \\ T_{sp} \leq 135 \ ^{\circ}\ C & -1 \\ \hline $\delta = 0.5; \ f = 20 \ kHz; \ square wave; \\ T_{sp} \leq 135 \ ^{\circ}\ C & -1 \\ \hline $non-repetitive peak forward current & $t_p \leq 1 \ ms; \ \delta \leq 0.25 & -1 \\ non-repetitive peak forward current & $t_p = 8 \ ms; \ T_{j(init)} = 25 \ ^{\circ}\ C; \ square wave \\ \ forware & t_p = 8 \ ms; \ T_{j(init)} = 25 \ ^{\circ}\ C; \ square wave & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq 25 \ ^{\circ}\ C & -1 \\ \hline $total power dissipation & $T_{amb} \leq -1 \\ \hline $total power dissipation & $T_{amb} \leq -1 \\ \hline $total power dissipation & $T_{amb} \leq -1 \\ \hline $total power dissipation & $T_{amb} \leq -1 \\ \hline $total power dissipation & $T_{amb} = $T_{amb$	$ \begin{array}{cccc} reverse \ voltage & T_{j} = 25 \ ^{\circ}\ C & - & 40 \\ \hline forward \ current & T_{sp} \leq 130 \ ^{\circ}\ C & - & 2.1 \\ average \ forward \ current & $\delta = 0.5; \ f = 20 \ kHz; \ square \ wave; \\ T_{amb} \leq 65 \ ^{\circ}\ C & 1.5 \\ \hline T_{amb} \leq 65 \ ^{\circ}\ C & - & 1.5 \\ \hline \delta = 0.5; \ f = 20 \ kHz; \ square \ wave; \\ T_{sp} \leq 135 \ ^{\circ}\ C & - & 1.5 \\ \hline repetitive \ peak \ forward \ current & t_{p} \leq 1 \ ms; \ \delta \leq 0.25 & - & 4 \\ non-repetitive \ peak \ forward \ t_{p} = 8 \ ms; \ T_{j(init)} = 25 \ ^{\circ}\ C; \ square \ wave \\ total \ power \ dissipation & t_{p} = 8 \ ms; \ T_{j(init)} = 25 \ ^{\circ}\ C; \ square \ wave \\ \hline 113 & - & 415 \\ \hline 113 & - & 895 \\ \hline 113 & - & 1505 \\ \hline junction \ temperature & & & & & & & & & & & & \\ mbient \ temperature & & & & & & & & & & & & & & & & \\ \hline mbient \ temperature & & & & & & & & & & & & & & & & & & &$

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Reflow soldering is the only recommended soldering method.

[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

### 6. Thermal characteristics

#### Table 6.Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air [1][2][3] [1][4][3]	[1][2][3]	-	-	300	K/W
	from junction to ambient		-	-	140	K/W	
			[1][5][3]	-	-	80	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		<u>[6]</u>	-	-	20	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub>are a significant part of the total power losses.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Reflow soldering is the only recommended soldering method.

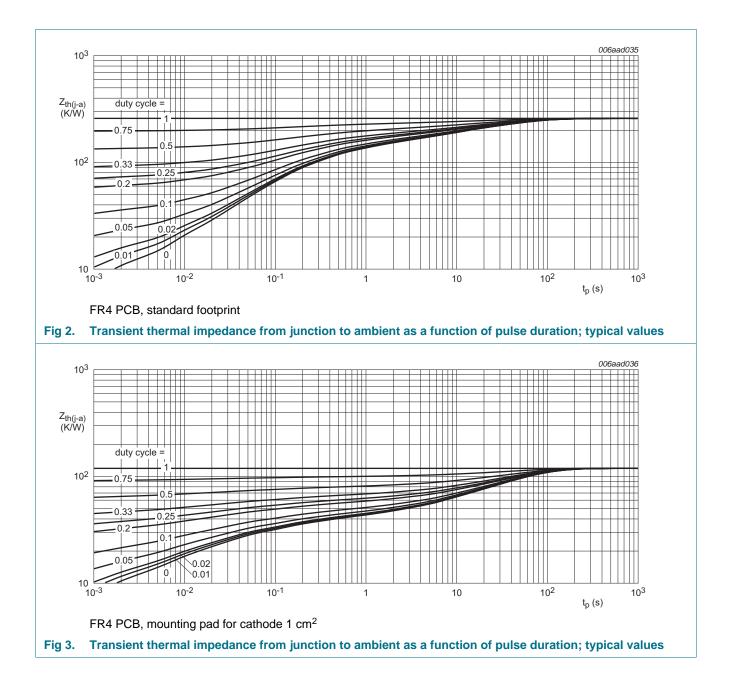
[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

[5] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.

[6] Soldering point of cathode tab.

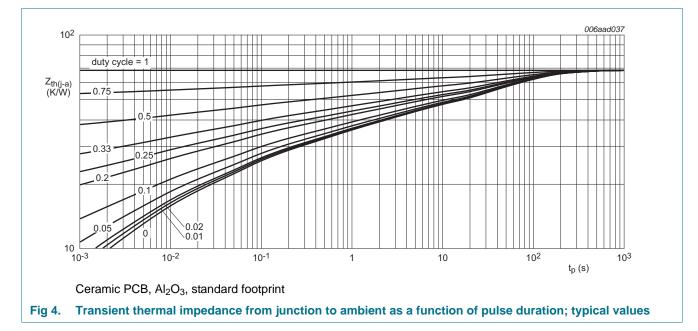
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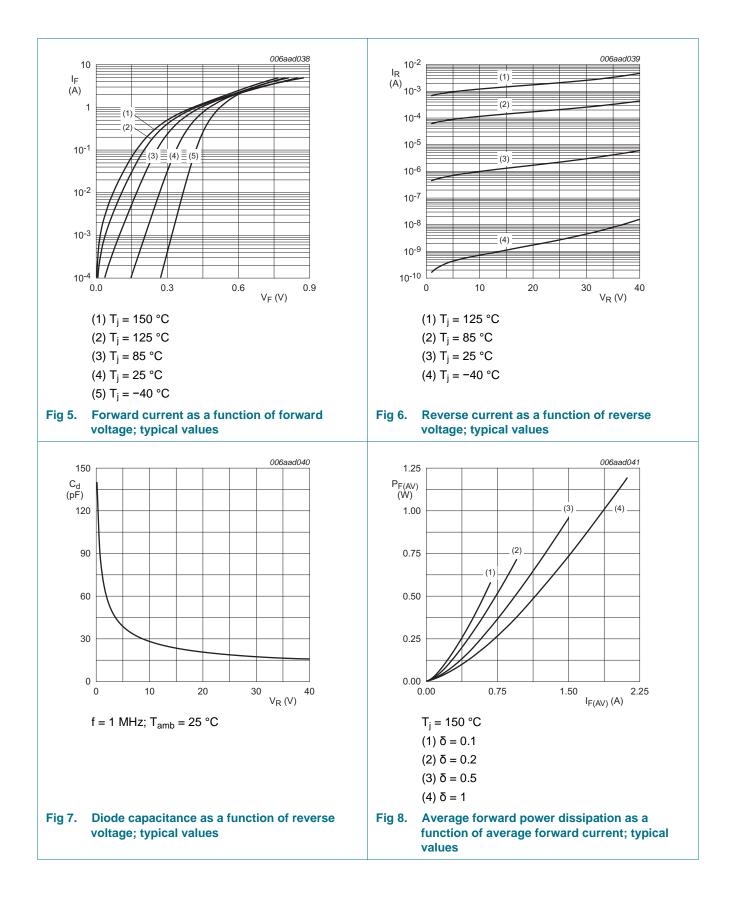


### 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>F</sub>	forward voltage	$I_F$ = 100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C	-	330	380	mV
		$I_F$ = 500 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C	-	415	480	mV
		$I_F$ = 1 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C	-	490	550	mV
		$I_F$ = 1.5 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C	-	540	610	mV
I <sub>R</sub>	reverse current	$V_R = 10 \text{ V}; \text{ T}_j = 25 \text{ °C}$	-	1	5	μA
		$V_R = 40 \text{ V}; \text{ T}_j = 25 \text{ °C}$	-	8	30	μA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	75	90	pF
		$V_R = 10 V$ ; f = 1 MHz; T <sub>j</sub> = 25 °C	-	30	40	pF
t <sub>rr</sub>	reverse recovery time	$ I_{F} = 0.5 \text{ A}; I_{R} = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A}; \\ T_{j} = 25 \text{ °C} $	-	4	-	ns
$V_{FRM}$	peak forward recovery voltage	$I_F = 0.5 \text{ A}; \text{ d}I_F/\text{d}t = 20 \text{ A}/\mu\text{s}; \text{ T}_j = 25 \text{ °C}$	-	440	-	mV

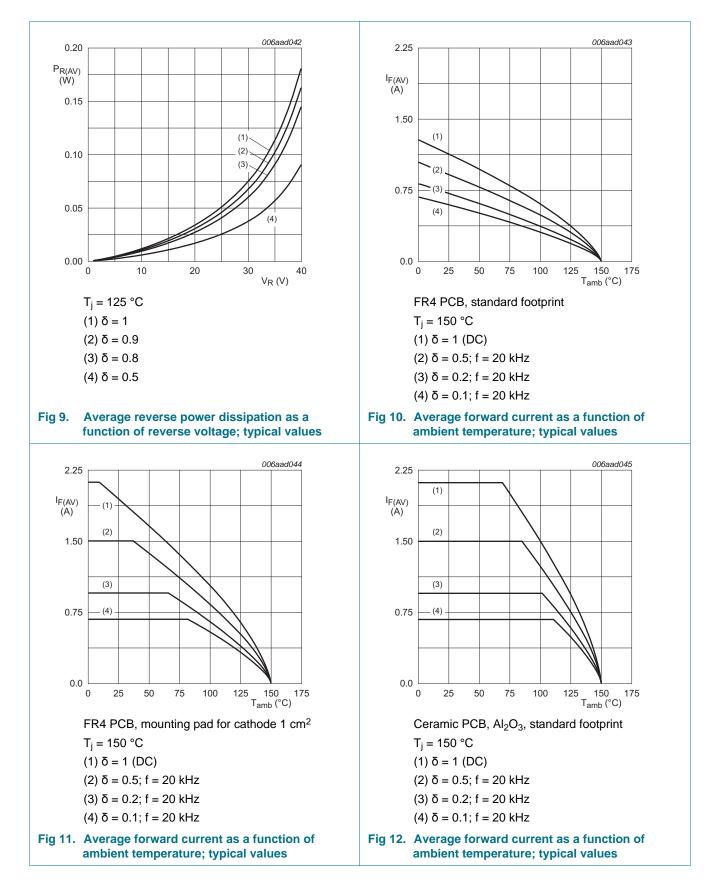
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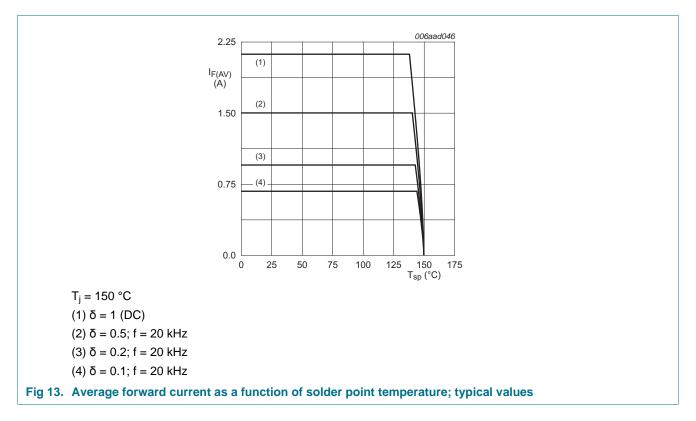


Product data sheet

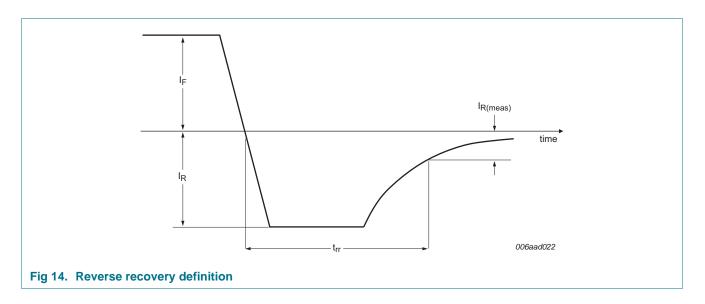
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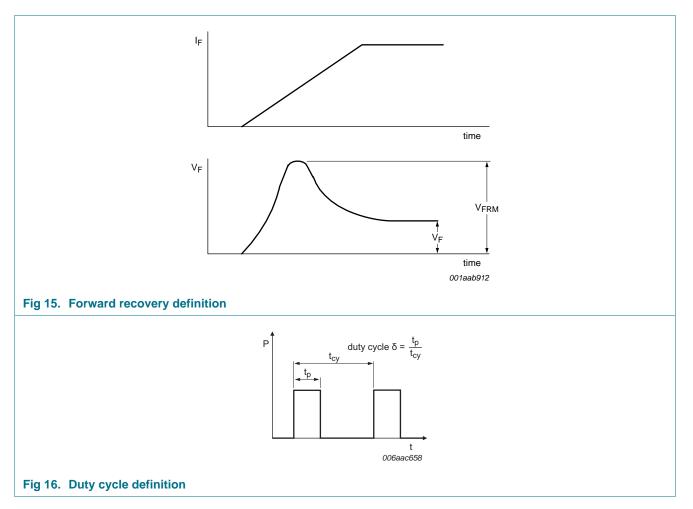
### 8. Test information



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The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

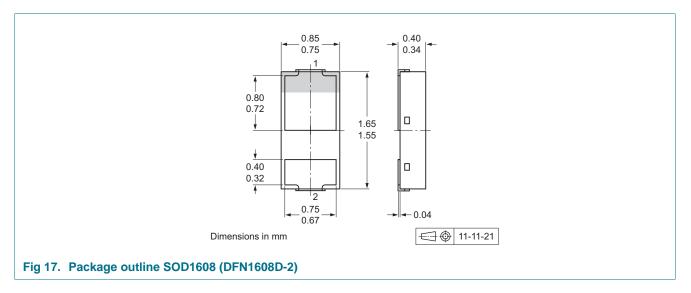
#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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#### **Package outline** 9.



### **10. Soldering**

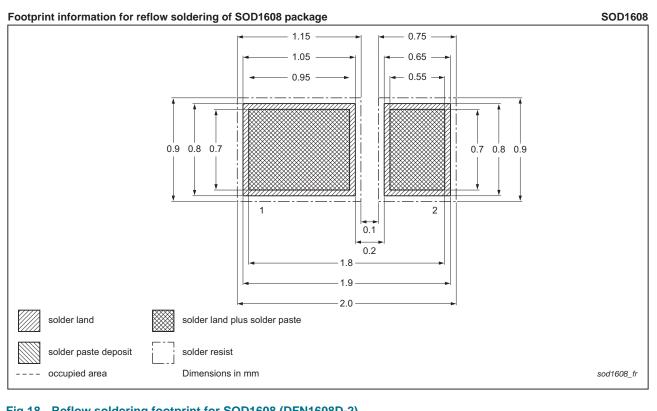


Fig 18. Reflow soldering footprint for SOD1608 (DFN1608D-2)

PMEG4015EPK **Product data sheet** 

40 V, 1.5 A low VF MEGA Schottky barrier rectifier

### **11. Revision history**

Table 8. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG4015EPK v.2	20120306	Product data sheet	-	PMEG4015EPK v.1
Modifications:	• Fig 14. and 15: co	orrected title		
PMEG4015EPK v.1	20120302	Product data sheet	-	-

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### 12. Legal information

### 12.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions'

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